

# PHX20N06T,127 Information



For Reference Only

Part Number PHX20N06T,127

Manufacturer NXP

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 55V 12.9A SOT186A

Package TO-220-3 Full Pack, Isolated Tab

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









# PHX20N06T,127 Specifications

Manufacturer Part Number         PHX20N06T,127           Manufacturer         NXP           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3 Full Pack, Isolated Tab           Series         TrenchMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         55V           Current - Continuous Drain (Id) @ 25°C         12.9A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 1mA           Gate Charge (Qg) (Max) @ Vgs         9.8nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         320pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         23W (Tc)           Rds On (Max) @ Id, Vgs         75 mOhm @ 10A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3 Full Pack, Isolated Tab		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-220-3 Full Pack, Isolated Tab  Series  TrenchMOS?  FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Torin to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  230pF @ 25V  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  75 mOhm @ 10A, 10V  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  Package / Case  TO-220-3 Full Pack, Isolated Tab	Manufacturer Part Number	PHX20N06T,127
Package         TO-220-3 Full Pack, Isolated Tab           Series         TrenchMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         55V           Current - Continuous Drain (Id) @ 25°C         12.9A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ ImA           Gate Charge (Qg) (Max) @ Vgs         9.8nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         320pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         23W (Tc)           Rds On (Max) @ Id, Vgs         75 mOhm @ 10A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3 Full Pack, Isolated Tab	Manufacturer	NXP
Package TO-220-3 Full Pack, Isolated Tab  Series TrenchMOS?  FET Type N-Channel  Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C 12.9A (Tc)  Drive Voltage (Max Rds On, Min Rds On) 10V  Vgs(th) (Max) @ Id 4V @ ImA  Gate Charge (Qg) (Max) @ Vgs 9.8n C @ 10V  Input Capacitance (Ciss) (Max) @ Vds 320pF @ 25V  Vgs (Max) ±20V  FET Feature - Power Dissipation (Max) 23W (Tc)  Rds On (Max) @ Id, Vgs 75 mOhm @ 10A, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220-3  Package / Case Tore Total Pack, Isolated Tab	Category	Discrete Semiconductor Products
Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 12.9A (Tc)  Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 9.8nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 320pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 23W (Tc) Rds On (Max) @ Id, Vgs 75 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case Touton (Max) NOSFET (Max) Input Capacitance (Ciss) (Max) @ To-220-3 Full Pack, Isolated Tab		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 12.9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ ImA Gate Charge (Qg) (Max) @ Vgs 9.8nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 320pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 23W (Tc) Rds On (Max) @ Id, Vgs 75 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case To-220-3 Full Pack, Isolated Tab	Package	TO-220-3 Full Pack, Isolated Tab
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  **EUV**  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Package / Case  MOSFET (Metal Oxide)  55V  55V  (Metal Oxide)  55V  55V  55V  55V  10V  529A (Te)  75 mOhm @ 10A, 10V	Series	TrenchMOS?
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  Package / Case  55V  12.9A (Tc)  10V  4V @ 1mA  4V @ 1mA  9.8nC @ 10V  320pF @ 25V  ±20V  FET Feature  -  To-220-3  Through Hole  TO-220-3 Full Pack, Isolated Tab	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  75 mOhm @ 10A, 10V  Operating Temperature  Supplier Device Package  Package / Case  12.9A (Tc)  10.9	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  4V @ 1mA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  **ET Feature**  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  75 mOhm @ 10A, 10V  Operating Temperature  **Operating Temperature**  Mounting Type  Through Hole  Supplier Device Package  Package / Case  **TO-220-3 Full Pack, Isolated Tab	Drain to Source Voltage (Vdss)	55V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  +20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  75 mOhm @ 10A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3 Full Pack, Isolated Tab	Current - Continuous Drain (Id) @ 25°C	12.9A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  #20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Through Hole  Supplier Device Package  TO-220-3  Full Pack, Isolated Tab	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  320pF @ 25V  Vgs (Max)  ET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  75 mOhm @ 10A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3 Full Pack, Isolated Tab	Vgs(th) (Max) @ Id	4V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)23W (Tc)Rds On (Max) @ Id, Vgs75 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Gate Charge (Qg) (Max) @ Vgs	9.8nC @ 10V
FET Feature - Case - Ca	Input Capacitance (Ciss) (Max) @ Vds	320pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  75 mOhm @ 10A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3 Full Pack, Isolated Tab	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs75 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3 Full Pack, Isolated Tab	Power Dissipation (Max)	23W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Rds On (Max) @ Id, Vgs	75 mOhm @ 10A, 10V
Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack, Isolated Tab	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3
Report errors?	Package / Case	TO-220-3 Full Pack, Isolated Tab
		Report errors?

## PHX20N06T,127 Guarantees



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## PHX20N06T,127 Payment Methods



















## PHX20N06T,127 Shipping Methods













If you have any question about PHX20N06T,127, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com